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(71) Applicant *(for all designated States except US)*: **LAM RESEARCH CORPORATION** [US/US]; 4650 Research Parkway, Fremont, CA 94538 (US).

(72) Inventors; and

(75) Inventors/Applicants *(for US only)*: **FU, Qian** [CN/US]; 3842 Northumberland Terrace, Fremont, CA 94555 (US). **LIU, Shenjian** [CN/US]; 2644 Cabot Court, Fremont, CA 94536 (US). **LEE, Linda, Fung-Ming** [US/US]; 759 Praderia Circle, Fremont, CA 94539 (US).

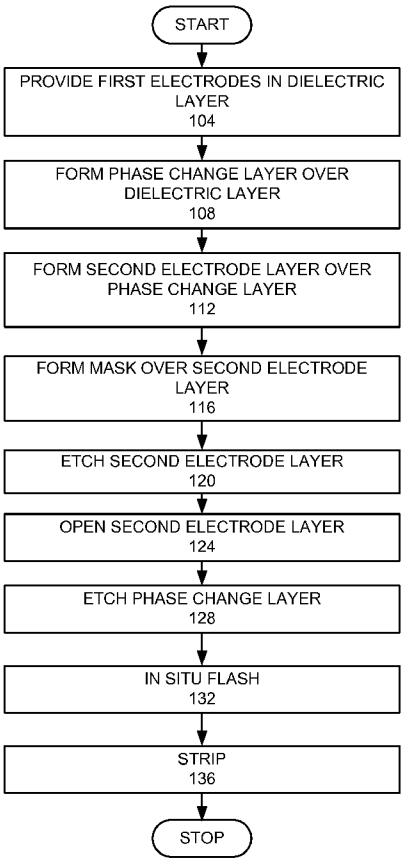
(74) Agents: **LEE, Michael, B., K.** et al.; Beyer Weaver LLP, P.O. Box 70250, Oakland, CA 94612-0250 (US).

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(54) Title: PHASE CHANGE ALLOY ETCH



(57) Abstract: A method of forming devices is provided. A phase change layer is provided. The phase change layer is etched by providing an etch gas comprising a bromine containing compound and forming a plasma from the etch gas. The phase change layer is of a material that may be heated by a current and then when cooled, either forms an amorphous material or a crystalline material, depending on how fast the material is cooled. In addition, the amorphous material has a resistance at least several times greater than the crystalline material.

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